TIGER ELECTRONIC CO.,LTD

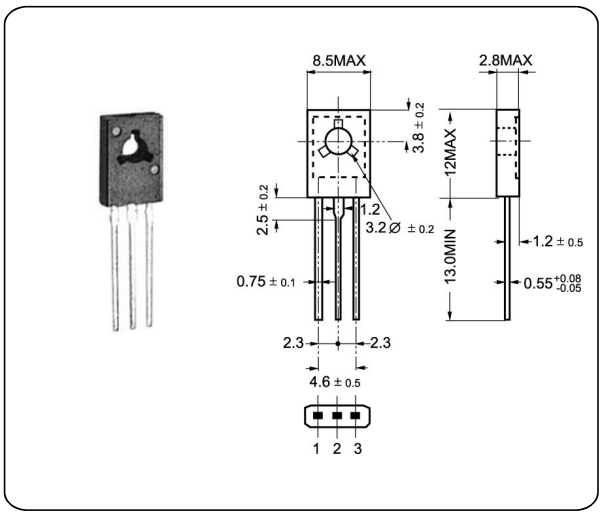
Product specification

Thyristors logic level — C106M

GENERAL DESCRIPTION

Passivated, sensitive gate thyristor in a plastic envelope, intended for use in general purpose switching and phase control applications. This device is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits

Parameter	Symbol	Max	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	400	V
Average on-state current	$I_{T(AV)}$	2.5	A
RMS on-state current	$I_{T(RMS)}$	4.0	A
Non-repetitive peak on-state current	I_{TSM}	38	A
Max. Operating Junction Temperature	T_j	110	°C
Storage Temperature	T_{stg}	-45~150	°C



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}		400			V
Average on-state current	$I_{T(AV)}$	half sine wave; T_{mb}< 103 °C		2.5		A
RMS on-state current	$I_{T(RMS)}$	all conduction angles		4.0		A
On-state voltage	V_T	I_T=5.0A		1.23	1.8	V
Holding current	I_H	V_D =12 V; I_{GT} = 0.1 A		0.1	6.0	mA
Latching current	I_L	V_D =12 V; I_{GT} = 0.1 A		0.17	10	mA
Gate trigger current	I_{GT}	V_D =12 V; I_T = 0.1 A		15	200	uA
Gate trigger voltage	V_{GT}	V_D =12 V; I_T = 0.1 A		0.4	1.5	V